

**JST08K-800C 8A TRIAC**

Rev.A.1.1

The JST08K-800C triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Package TO-252 is RoHS compliant.

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c = 91^\circ\text{C}$)	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	80	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		88	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	32	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	-	80	$\text{A}/\mu\text{s}$
	-	40	
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.8)	V_{PP}	1.5	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33	- -	MAX.	25	mA
				50	
V _{GT}		ALL	MAX.	1	V
V _{GD}	V _D =V _{DRM} T _j =125 R _L =3.3k	ALL	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	- -	MAX.	40	mA
				80	
I _H	I _T =200mA		MAX.	30	mA
dV/dt	V _D =540V Gate Open T _j =125		MIN.	500	V/μs
(dV/dt) _c	(dI/dt) _c =3.5A/ms, T _j =125		MIN.	6	V/μs
t _{on}	I _G =80mA I _A =400mA I _R =40mA T _j =25		TYP.	5	μs
t _{off}				30	

Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	I _{TM} =11A t _p =380μs	T _j =25	1.5	V
V _{TO}	Threshold voltage	T _j =125	0.8	V
R _D	Dynamic resistance	T _j =125	44	m
I _{DRM}	V _D =V _{DRM} V _R =V _{RDM}	T _j =25	5	μA
I _{RDM}		T _j =125	0.35	mA

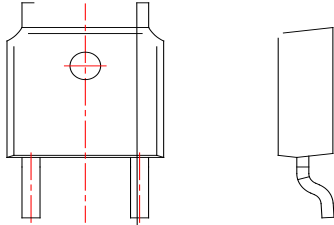
Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case (AC)	3	/W
R _{th(j-a)}	junction to ambient (AC)	100	/W

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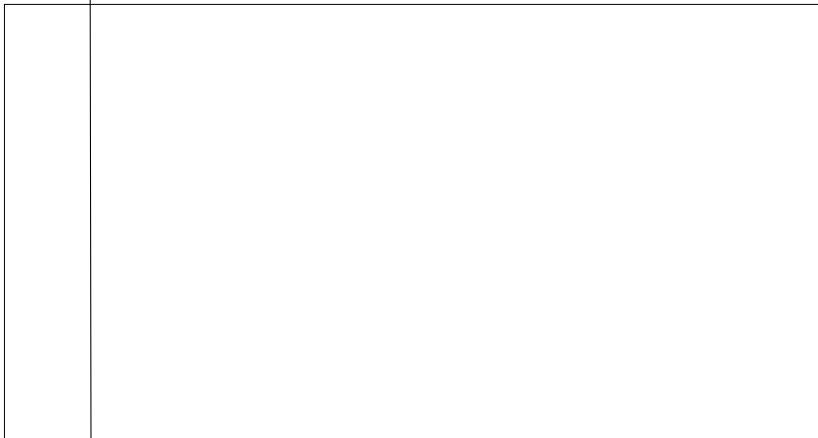
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Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.15	0		0.006
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1						
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
G1	2.18		2.38	0.086		0.094
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065





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